

Low Voltage Buffer/Line **Driver with 5V Tolerant Inputs and Outputs** 74LCX244

The LCX244 contains eight non-inverting buffers with 3-STATE outputs. The device may be employed as a memory address driver, clock driver and bus-oriented transmitter/receiver. The LCX244 is designed for low voltage (2.5 V or 3.3 V) V_{CC} applications with capability of interfacing to a 5 V signal environment.

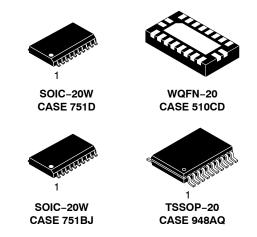
The LCX244 is fabricated with an advanced CMOS technology to achieve high speed operation while maintaining CMOS low power dissipation.

Features

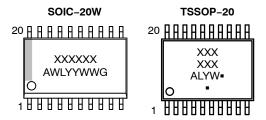
- 5 V Tolerant Inputs and Outputs
- 1.65 V to 5.5 V V_{CC} Specifications Provided
- 6.5 ns t_{PD} max. ($V_{CC} = 3.3 \text{ V}$), 10 μ A I_{CC} max.
- Power Down High Impedance Inputs and Outputs
- Supports Live Insertion/Withdrawal (Note 1)
- ± 24 mA Output Drive ($V_{CC} = 3.0 \text{ V}$)
- Implements Proprietary Noise/EMI Reduction Circuitry
- Latch-up Performance Exceeds 500 mA
- ESD Performance:

July, 2024 - Rev. 2

- Human Body Model > 2000 V
- Leadless DQFN Package
- 1. To ensure the high-impedance state during power up or down, \overline{OE} should be tied to V_{CC} through a pull-up resistor: the minimum value or the resistor is determined by the current-sourcing capability of the driver.



MARKING DIAGRAMS



XXXXXX = Specific Device Code = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

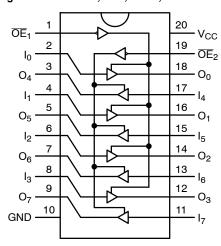
(Note: Microdot may be in either location)

ORDERING INFORMATION

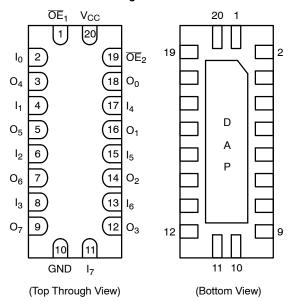
See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

Connection Diagram

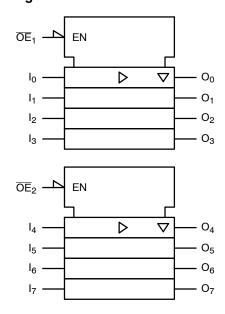
Pin Assignments for SOIC, SOP, SSOP, and TSSOP



Pad Assignments for DQFN



Logic Diagram



Truth Tables

Inp	uts	Outputs
ŌE ₁	l _n	(Pins 12, 14, 16, 18)
L	L	L
L	Н	Н
Н	Х	Z

Inputs		Outputs
OE ₂	l _n	(Pins 3, 5, 7, 9)
L	L	L
L	Н	Н
Н	Х	Z

H = HIGH Voltage Level

L = LOW Voltage Level X = Immaterial

Z = High Impedance

PIN DESCRIPTION

Pin Names	Description
$\overline{OE}_1, \overline{OE}_2$	3-STATE Output Enable Inputs
I ₀ -I ₇	Inputs
$\overline{O}_0 - \overline{O}_7$	Outputs
DAP	No Connect

2. DAP (Die Attach Pad)

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
VI	DC Input Voltage (Note 3)		-0.5 to +6.5	V
Vo		Mode (High or Low State) Tri-State Mode -Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} +0.5 -0.5 to +6.5 -0.5 to +6.5	٧
I _{IK}	DC Input Diode Current	V _{IN} < GND	-50	mA
lok	DC Output Diode Current	V _{OUT} < GND	-50	mA
Ιο	DC Output Source/Sink Current	±50	mA	
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C	
T_L	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 4)	SOIC-20W WQFN20 TSSOP-20	96 99 150	°C/W
P _D	Power Dissipation in Still Air	SOIC-20W WQFN20 TSSOP-20	1302 1256 833	mW
MSL	Moisture Sensitivity	SOIC-20W All Other Packages	Level 3 Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 5)	Human Body Model Charged Device Model	2000 N/A	٧

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS (Note 6)

Symbol	P	Min	Max	Unit	
V _{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	5.5 5.5	V
VI	Digital Input Voltage		0	5.5	V
V _O	Output Voltage	Active Mode (High or Low State) Tri-State Mode Power Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	V
T _A	Operating Free-Air Temperature		-40	+125	°C
t _r , t _f	Input Rise or Fall Rate	$\begin{array}{c} V_{CC} = 1.65 \text{ V to } 1.95 \text{ V} \\ V_{CC} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{IN} \text{ from } 0.8 \text{ V to } 2.0 \text{ V, } V_{CC} = 3.0 \text{ V} \\ V_{CC} = 4.5 \text{ V to } 5.5 \text{ V} \end{array}$	0 0 0	20 20 10 5	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

6. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

I_O absolute maximum rating must be observed.
 Measured with minimum pad spacing on an FR4 board, using 76mm-by-114mm, 2-ounce copper trace no air flow per JESD51-7.

^{5.} HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A.

DC ELECTRICAL CHARACTERISTICS

					$T_A = -40^{\circ}C$ to +85°C		$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input		1.65 to 1.95	0.65 x V _{CC}		0.65 x V _{CC}		V
	Voltage		2.3 to 2.7	1.7		1.7		
			2.7 to 3.6	2.0		2.0		
			4.5 to 5.5	0.7 x V _{CC}		0.7 x V _{CC}		1
V _{IL}	Low-Level Input		1.65 to 1.95		0.35 x V _{CC}		0.35 x V _{CC}	V
	Voltage		2.3 to 2.7		0.7		0.7	
			2.7 to 3.6		0.8		0.8	
			4.5 to 5.5		0.3 x V _{CC}		0.3 x V _{CC}	
V _{OH}	High-Level Output	$V_I = V_{IH}$ or V_{IL}	•		•	•	•	V
	Voltage	I _{OH} = -100 μA	1.65 to 5.5	V _{CC} – 0.1	_	V _{CC} – 0.1	-	
		I _{OH} = -4 mA	1.65	1.2	-	1.2	-	
		I _{OH} = -8 mA	2.3	1.8	_	1.8	-	1
		I _{OH} = -12 mA	2.7	2.2	_	2.2	-	1
		I _{OH} = -16 mA	3.0	2.4	_	2.4	-	1
		I _{OH} = -24 mA	3.0	2.2	_	2.2	-	1
		I _{OH} = -32 mA	4.5	3.8		3.8		1
V _{OL}	Low-Level Output	$V_I = V_{IH}$ or V_{IL}						V
	Voltage	I _{OL} = 100 μA	1.65 to 5.5	=	0.1	-	0.1	
		I _{OL} = 4 mA	1.65	=	0.45	-	0.45	
		I _{OL} = 8 mA	2.3	_	0.6	-	0.6	
		I _{OL} = 12 mA	2.7	_	0.4	-	0.4	
		I _{OL} = 16 mA	3.0	_	0.4	-	0.4	
		I _{OL} = 24 mA	3.0	_	0.55	-	0.55	
		I _{OL} = 32 mA	4.5		0.6		0.6	
l _l	Input Leakage Current	V _I = 0 to 5.5 V	3.6	-	±5.0	-	±5.0	μА
I _{OZ}	3-State Output Leakage Current	$V_I = V_{IH} \text{ or } V_{IL},$ $V_O = 0 \text{ V to 5.5 V}$	3.6	-	±5.0	-	±5.0	μΑ
I _{OFF}	Power Off Leakage Current	V _I = 5.5 V or V _O = 5.5 V	0	-	10	-	10	μΑ
I _{CC}	Quiescent Supply	V _I = 5.5 V or GND	2.3 to 3.6	-	10	-	10	μΑ
	Current	3.6 V ≤ V _I , V _O ≤ 5.5 V (Note 7)			±10.0		±10.0	
ΔI_{CC}	Increase in I _{CC} per Input	$V_{IH} = V_{CC} - 0.6 V$	2.3 to 3.6	-	500	-	500	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Outputs disabled or 3–STATE only.

AC ELECTRICAL CHARACTERISTICS

				T _A = -40°	C to +85°C	T _A = -40°C	C to +125°C	
Symbol	Parameter	Test Condition	tion V _{CC} (V)	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation	See Figures	1.65 to 1.95	-	10.3	_	10.3	ns
	Delay, D to O	1 and 2	2.3 to 2.7	-	7.8	_	7.8	1
			2.7	-	7.5	_	7.5	1
			3.0 to 3.6	-	6.5	_	6.5	1
			4.5 to 5.5	-	5.9	_	5.9	1
t _{PZH} , t _{PZL}	Output Enable	See Figures	1.65 to 1.95	-	13.0	_	13.0	ns
	Time, OE to O	1 and 2	2.3 to 2.7	-	10.0	_	10.0	1
			2.7	-	9.0	_	9.0	1
			3.0 to 3.6	-	8.0	_	8.0	1
			4.5 to 5.5	-	7.3	_	7.3	1
t _{PHZ} , t _{PLZ}	Output Disable	See Figures	1.65 to 1.95	-	11.0	_	11.0	ns
	Time, OE to O	1 and 2	2.3 to 2.7	-	8.4	_	8.4	1
			2.7	-	8.0	_	8.0	1
			3.0 to 3.6	-	7.0	_	7.0	1
			4.5 to 5.5	-	6.0	_	6.0	1
t _{OSHL} , t _{OSLH}	Output to Output		1.65 to 1.95	-	_	_	-	ns
	Skew (Note 8)		2.3 to 2.7	-	_	-	-	
			2.7	-	_	-	-	
			3.0 to 3.6	-	1.0	_	1.0	1

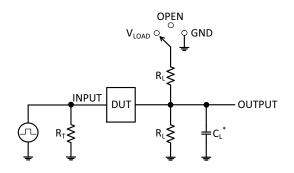
^{8.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I_{CC(OPR)} = C_{PD} x V_{CC} x f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption: P_D = C_{PD} x V_{CC}² x f_{in} + I_{CC} x V_{CC}.

DYNAMIC SWITCHING CHARACTERISTICS

				T _A = 25°C	
Symbol	Parameter	V _{CC} (V)	Conditions	Typical	Unit
V _{OLP}	Quiet Output Dynamic Peak V _{OL}	3.3	$C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	0.8	V
		2.5	C _L = 30 pF, V _{IH} = 2.5 V, V _{IL} = 0 V	0.6	
V _{OLV}	Quiet Output Dynamic Valley V _{OL}	3.3	C _L = 50 pF, V _{IH} = 3.3 V, V _{IL} = 0 V	-0.8	V
		2.5	$C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$	-0.6	

CAPACITANCE

Symbol	Parameter	Conditions	Typical	Unit
C _{IN}	Input Capacitance	V _{CC} = Open, V _I = 0 V or V _{CC}	7.0	pF
C _{OUT}	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	8.0	pF
C _{PD}	Power Dissipation Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}, f = 10 \text{ MHz}$	25.0	pF



Test	Switch Position
t _{PLH} / t _{PHL}	Open
t _{PLZ} / t _{PZL}	V_{LOAD}
t _{PHZ} / t _{PZH}	GND

V_{cc}

- GND

~0 V

*CL includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 1. Test Circuit

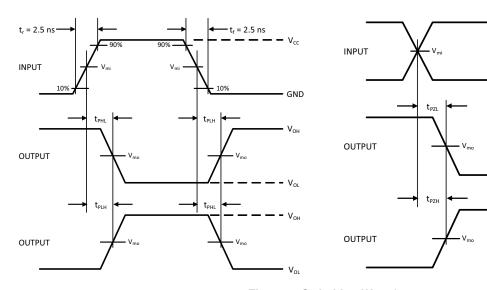
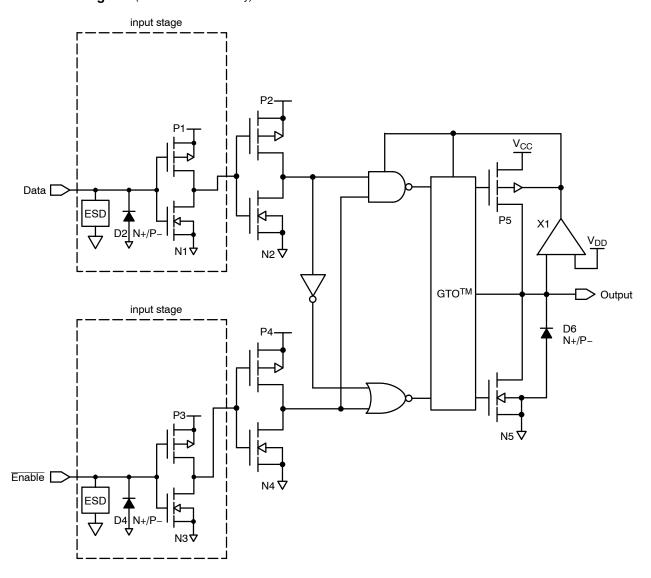


Figure 2. Switching Waveforms

V _{CC} , V	R_L, Ω	C _L , pF	V_{LOAD}	V _{mi} , V	V_{mo}, V	V _Y , V
1.65 to 1.95	500	30	2 x V _{CC}	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	500	30	2 x V _{CC}	V _{CC} /2	V _{CC} /2	0.15
2.7	500	50	6 V	1.5	V _{CC} /2	0.3
3.0 to 3.6	500	50	6 V	1.5	V _{CC} /2	0.3
4.5 to 4.5	500	50	2 x V _{CC}	V _{CC} /2	V _{CC} /2	0.3

Schematic Diagram (Generic for LCX Family)



ORDERING INFORMATION

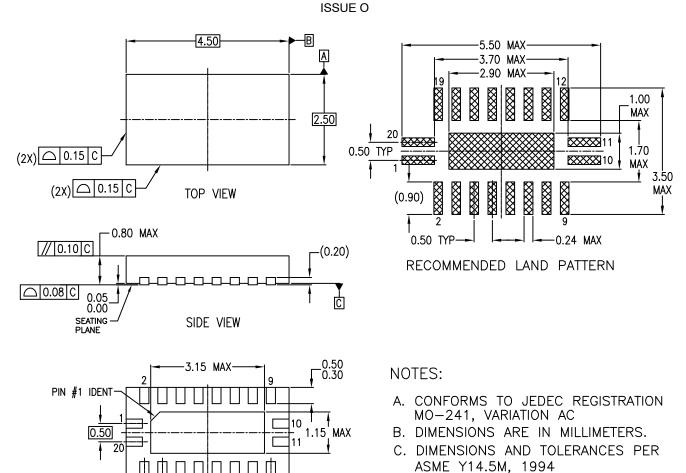
Device	Marking	Package	Shipping [†]
74LCX244WM	LCX244	SOIC-20 WB	38 Units / Tube
74LCX244WMX	LCX244	SOIC-20 WB	1000 / Tape & Reel
74LCX244MTC	LCX 244	TSSOP-20	75 Units / Tube
74LCX244MTCX	LCX 244	TSSOP-20	2500 / Tape & Reel
74LCX244BQX	LCX244	WQFN20, 2.5x4.5	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*-}Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

WQFN20 4.5x2.5, 0.5PCASE 510CD



3.50

0.50

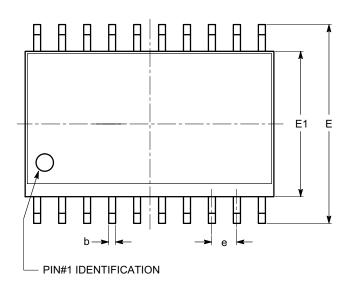
12

0.18 - 0.30

⊕ 0.10(M) C A B 0.05(M) C

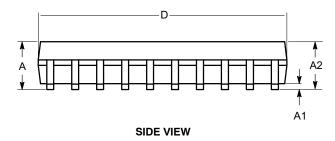
PACKAGE DIMENSIONS

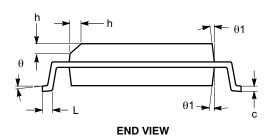
SOIC-20, 300 mils CASE 751BJ ISSUE O



SYMBOL	MIN	NOM	MAX
Α	2.36	2.49	2.64
A1	0.10		0.30
A2	2.05		2.55
b	0.31	0.41	0.51
С	0.20	0.27	0.33
D	12.60	12.80	13.00
Е	10.01	10.30	10.64
E1	7.40	7.50	7.60
е	1.27 BSC		
h	0.25		0.75
L	0.40	0.81	1.27
θ	0°		8°
θ1	5°		15°

TOP VIEW



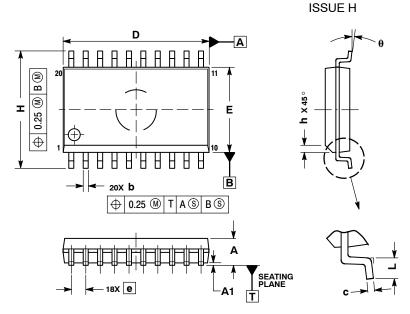


Notes:

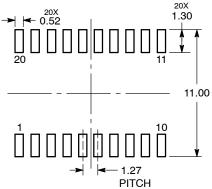
- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MS-013.

PACKAGE DIMENSIONS

SOIC-20 WB CASE 751D-05



RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

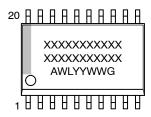
NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
- PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION
 SHALL BE 0.13 TOTAL IN EXCESS OF B
- DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
b	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27 BSC		
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0 °	7 °	

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location Α

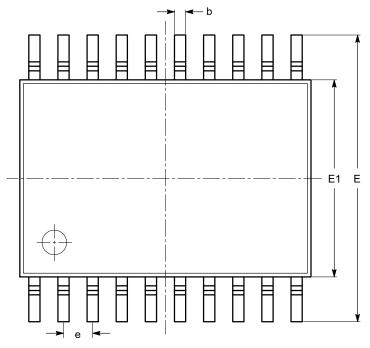
WL = Wafer Lot YY = Year ww = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

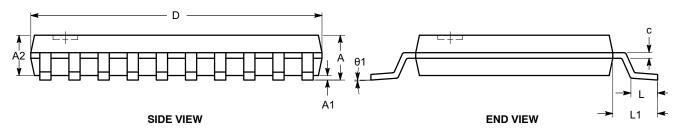
PACKAGE DIMENSIONS

TSSOP20, 4.4x6.5 CASE 948AQ **ISSUE A**



SYMBOL	MIN	NOM	MAX
Α			1.20
A1	0.05		0.15
A2	0.80		1.05
b	0.19		0.30
С	0.09		0.20
D	6.40	6.50	6.60
Е	6.30	6.40	6.50
E1	4.30	4.40	4.50
е	0.65 BSC		
L	0.45	0.60	0.75
L1	1.00 REF		
θ	0°		8°

TOP VIEW



Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MO-153.

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